

STN	Polovodičové súčiastky Mechanické a klimatické skúšobné metódy Časť 28: Skúšanie citlivosti na elektrostatický výboj (ESD) Model nabitej súčiastky (CDM) - úroveň zariadenia	STN EN 60749-28 35 8799
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Semiconductor devices - Mechanical and climatic test methods - Part 28: Electrostatic discharge (ESD) sensitivity testing - Charged device model (CDM) - device level

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Part 28: Electrostatic discharge (ESD) sensitivity testing -
Charged device model (CDM) - device level
(IEC 60749-28:2017)

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mécaniques et climatiques - Partie 28: Essai de sensibilité
aux décharges électrostatiques (DES) - Modèle de dispositif
chargé par contact direct (DC-CDM)
(IEC 60749-28:2017)

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Model (CDM) - Device Level
(IEC 60749-28:2017)

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EN 60749-28:2017**European foreword**

The text of document 47/2362/FDIS, future edition 1 of IEC 60749-28, prepared by IEC/TC 47 "Semiconductor devices" in collaboration with IEC/TC 101 "Electrostatics" was submitted to the IEC-CENELEC parallel vote and approved by CENELEC as EN 60749-28:2017.

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IEC 60749-26 NOTE Harmonized as EN 60749-26.



INTERNATIONAL STANDARD



**Semiconductor devices – Mechanical and climatic test methods –
Part 28: Electrostatic discharge (ESD) sensitivity testing – Charged device
model (CDM) – device level**



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**Semiconductor devices – Mechanical and climatic test methods –
Part 28: Electrostatic discharge (ESD) sensitivity testing – Charged device
model (CDM) – device level**

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CONTENTS

FOREWORD.....	5
INTRODUCTION.....	7
1 Scope.....	8
2 Normative references	8
3 Terms and definitions	8
4 Required equipment	9
4.1 CDM ESD tester	9
4.1.1 General	9
4.1.2 Current-sensing element.....	10
4.1.3 Ground plane.....	10
4.1.4 Field plate/field plate dielectric layer.....	10
4.1.5 Charging resistor	11
4.2 Waveform measurement equipment	11
4.2.1 General	11
4.2.2 Cable assemblies	11
4.2.3 Equipment for high-bandwidth waveform measurement	11
4.2.4 Equipment for 1,0 GHz waveform measurement	11
4.3 Verification modules (metal discs).....	11
4.4 Capacitance meter.....	11
4.5 Ohmmeter.....	12
5 Periodic tester qualification, waveform records, and waveform verification requirements	12
5.1 Overview of required CDM tester evaluations.....	12
5.2 Waveform capture hardware	12
5.3 Waveform capture setup	12
5.4 Waveform capture procedure	12
5.5 CDM tester qualification/requalification procedure	13
5.5.1 CDM tester qualification/requalification procedure	13
5.5.2 Conditions requiring CDM tester qualification/requalification.....	13
5.5.3 1 GHz oscilloscope correlation with high bandwidth oscilloscope	14
5.6 CDM tester quarterly and routine waveform verification procedure	14
5.6.1 Quarterly waveform verification procedure	14
5.6.2 Routine waveform verification procedure	14
5.7 Waveform characteristics	14
5.8 Documentation.....	16
5.9 Procedure for evaluating full CDM tester charging of a device	16
6 CDM ESD testing requirements and procedures	17
6.1 Device handling	17
6.2 Test requirements	17
6.2.1 Test temperature and humidity	17
6.2.2 Device test	17
6.3 Test procedures.....	17
6.4 CDM test recording / reporting guidelines	18
7 CDM classification criteria	18
Annex A (normative) Verification module (metal disc) specifications and cleaning guidelines for verification modules and testers.....	19

A.1	Tester verification modules and field plate dielectric	19
A.2	Care of verification modules.....	19
Annex B (normative)	Capacitance measurement of verification modules (metal discs) sitting on a tester field plate dielectric	20
Annex C (informative)	CDM test hardware and metrology improvements.....	21
Annex D (informative)	CDM tester electrical schematic	23
Annex E (informative)	Sample oscilloscope setup and waveform	24
E.1	General.....	24
E.2	Settings for the 1 GHz bandwidth oscilloscope.....	24
E.3	Settings for the high-bandwidth oscilloscope.....	24
E.4	Setup.....	24
E.5	Sample waveforms from a 1 GHz oscilloscope	24
E.6	Sample waveforms from an 8 GHz oscilloscope	25
Annex F (informative)	Field-induced CDM tester discharge procedures.....	27
F.1	General.....	27
F.2	Single discharge procedure.....	27
F.3	Dual discharge procedure	27
Annex G (informative)	Waveform verification procedures	29
G.1	Factor/offset adjustment method.....	29
G.2	Software voltage adjustment method.....	32
G.3	Example parameter recording tables	34
Annex H (informative)	Determining the appropriate charge delay for full charging of a large module or device.....	36
H.1	General.....	36
H.2	Procedure for charge delay determination.....	36
Annex I (informative)	Electrostatic discharge (ESD) sensitivity testing direct contact charged device model (DC-CDM).....	38
I.1	General.....	38
I.2	Standard test module	38
I.3	Test equipment (CDM simulator).....	38
I.3.1	Test equipment design.....	38
I.3.2	DUT (device under test) support	38
I.3.3	Metal bar/board	39
I.3.4	Equipment setup.....	39
I.4	Verification of test equipment.....	39
I.4.1	General description of verification test equipment.....	39
I.4.2	Instruments for measurement	41
I.4.3	Verification of test equipment, using a current probe	41
I.5	Test procedure.....	42
I.5.1	Initial measurement	42
I.5.2	Tests	42
I.5.3	Intermediate and final measurement	43
I.6	Failure criteria.....	43
I.7	Classification criteria.....	43
I.8	Summary	43
Bibliography.....		44
Figure 1 – Simplified CDM tester hardware schematic		10

Figure 2 – CDM characteristic waveform and parameters	16
Figure D.1 – Simplified CDM tester electrical schematic	23
Figure E.1 – 1 GHz TC 500, small verification module	25
Figure E.2 – 1 GHz TC 500, large verification module	25
Figure E.3 – 8 GHz TC 500, small verification module (oscilloscope adjusts for attenuation)	26
Figure E.4 – GHz TC 500, large verification module (oscilloscope adjusts for attenuation)	26
Figure F.1 – Single discharge procedure (field charging, I_{CDM} Pulse, and slow discharge).....	27
Figure F.2 – Dual discharge procedure (field charging, 1st I_{CDM} pulse, no field, 2nd I_{CDM} pulse)	28
Figure G.1 – An example of a waveform verification flow for qualification and quarterly checks using the factor/offset adjustment method	30
Figure G.2 – An example of a waveform verification flow for the routine checks using the factor/offset adjustment method	31
Figure G.3 – Example of average I_{peak} for the large verification module – high bandwidth oscilloscope	32
Figure G.4 – An example of a waveform verification flow for qualification and quarterly checks using the software voltage adjustment method	33
Figure G.5 – An example of a waveform verification flow for the routine checks using the software voltage adjustment method	34
Figure H.1 – An example characterization of charge delay vs. I_{p}	37
Figure I.1 – Examples of discharge circuit where the discharge is caused by closing the switch	39
Figure I.2 – Verification test equipment for measuring the discharge current flowing to the metal bar/board from the standard test module	40
Figure I.3 – Current waveform.....	40
Figure I.4 – Measurement circuit for verification method using a current probe	41
Table 1 – CDM waveform characteristics for a 1 GHz bandwidth oscilloscope.....	15
Table 2 – CDM waveform characteristics for a high-bandwidth (≥ 6 GHz) oscilloscope.....	15
Table 3 – CDM ESDS device classification levels	18
Table A.1 – Specification for CDM tester verification modules (metal discs).....	19
Table G.1 – Example waveform parameter recording table for the factor/offset adjustment method	35
Table G.2 – Example waveform parameter recording table for the software voltage adjustment method	35
Table I.1 – Dimensions of the standard test modules	38
Table I.2 – Specified current waveform	40
Table I.3 – Range of peak current I_{p1} for test equipment.....	41
Table I.4 – Specification of peak current I_{p1} for the current probe verification method	42

INTERNATIONAL ELECTROTECHNICAL COMMISSION

**SEMICONDUCTOR DEVICES –
MECHANICAL AND CLIMATIC TEST METHODS –****Part 28: Electrostatic discharge (ESD) sensitivity testing –
Charged device model (CDM) – device level**

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International Standard IEC 60749-28 has been prepared by IEC technical committee 47: Semiconductor devices in collaboration with IEC technical committee 101: Electrostatics.

This standard is based on ESDA/JEDEC Joint Standard ANSI/ESDA/JEDEC JS-002 which resulted from the merging of JESD22-C101 and ANSI/ESD S5.3.1). It contains the essential elements from both standards. The co-operation of ANSI/ESDA/JEDEC is gratefully acknowledged.

The text of this International Standard is based on the following documents:

FDIS	Report on voting
47/2362/FDIS	47/2379/RVD

Full information on the voting for the approval of this International Standard can be found in the report on voting indicated in the above table.

This document has been drafted in accordance with the ISO/IEC Directives, Part 2.

A list of all parts in the IEC 60749 series, published under the general title *Semiconductor devices –Mechanical and climatic test methods*, can be found on the IEC website.

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INTRODUCTION

The earliest electrostatic discharge (ESD) test models and standards simulate a charged object approaching a device and discharging through the device. The most common example is IEC 60749-26, the human body model (HBM). However, with the increasing use of automated device handling systems, another potentially destructive discharge mechanism, the charged device model (CDM), becomes increasingly important. In the CDM, a device itself becomes charged (e.g. by sliding on a surface (tribocharging) or by electric field induction) and is rapidly discharged (by an ESD event) as it closely approaches a conductive object. A critical feature of the CDM is the metal-metal discharge, which results in a very rapid transfer of charge through an air breakdown arc. The CDM test method also simulates metal-metal discharges arising from other similar scenarios, such as the discharging of charged metal objects to devices at different potential.

Accurately quantifying and reproducing this fast metal-metal discharge event is very difficult, if not impossible, due to the limitations of the measuring equipment and its influence on the discharge event. The CDM discharge is generally completed in a few nanoseconds, and peak currents of tens of amperes have been observed. The peak current into the device will vary considerably depending on a large number of factors, including package type and parasitics. The typical failure mechanism observed in MOS devices for the CDM model is dielectric damage, although other damage has been noted.

The CDM charge voltage sensitivity of a given device is package dependent. For example, the same integrated circuit (IC) in a small area package can be less susceptible to CDM damage at a given voltage compared to that same IC in a package of the same type with a larger area. It has been shown that CDM damage susceptibility correlates better to peak current levels than charge voltage.

SEMICONDUCTOR DEVICES – MECHANICAL AND CLIMATIC TEST METHODS –

Part 28: Electrostatic discharge (ESD) sensitivity testing – Charged device model (CDM) – device level

1 Scope

This part of IEC 60749 establishes the procedure for testing, evaluating, and classifying devices and microcircuits according to their susceptibility (sensitivity) to damage or degradation by exposure to a defined field-induced charged device model (CDM) electrostatic discharge (ESD). All packaged semiconductor devices, thin film circuits, surface acoustic wave (SAW) devices, opto-electronic devices, hybrid integrated circuits (HICs), and multi-chip modules (MCMs) containing any of these devices are to be evaluated according to this document. To perform the tests, the devices are assembled into a package similar to that expected in the final application. This CDM document does not apply to socketed discharge model testers. This document describes the field-induced (FI) method. An alternative, the direct contact (DC) method, is described in Annex I.

The purpose of this document is to establish a test method that will replicate CDM failures and provide reliable, repeatable CDM ESD test results from tester to tester, regardless of device type. Repeatable data will allow accurate classifications and comparisons of CDM ESD sensitivity levels.

2 Normative references

There are no normative references in this document.

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